AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 5, line 15, and ending on page 6, line 7, with the following amended paragraph:

Recently, many attempts have been made to use the OTFT for various drive devices. However, to realize the practical use of OTFT in LCD or flexible displays using organic EL, not only should a charge mobility increase to the level of 5 $cm^2 \cdot V^{-1} \cdot sec^{-1}$ or higher, but also improvement in the driving and threshold voltages of the device should be achieved. In particular, for simplifying the preparation and reducing the cost, it can be desirable for the whole process of preparing the OTFT to be carried out by an all-printing or all-spin method on a plastic substrate. Under the circumstances, there have been many ~~researches~~ research efforts for developing a method to simplify the preparation of the organic gate insulating film and to increase the charge mobility in the interface between the insulator and the organic active layer. However, satisfactory results have yet to be obtained.

Please replace the paragraph beginning on page 6, line 15, and ending on page 6, line 24, with the following amended paragraph:

The present inventors devoted much effort to meet these demands and found that, when using a multi-layered gate insulator including a first layer of a high ~~K~~ k material and a second layer of an insulating polymer being compatible with an organic active layer and positioned directly beneath the organic active layer, the OTFT thus obtained exhibits a higher charge mobility and a lower driving and threshold voltages and its whole preparation can be achieved by a wet process, such as printing or spin coating.

Please replace the paragraph beginning on page 8, line 19, and ending on page 8, line 21, with the following amended paragraph:

As mentioned above, the layering order between the organic active layer and the source/drain electrode may be changed relative to each other.

Please replace the paragraph beginning on page 9, line 6, and ending on page 10, line 3, with the following amended paragraph:

In the present invention, the first layer of the gate insulating film is composed of a high k material having both high dielectric constant (k) and excellent insulating properties, and it is formed by a wet process. Specifically, the first insulating layer **2** is made of (1) a mixture of an insulating organic polymer and an organic metal compound having a dielectric constant of 5 or higher, or (2) a mixture of an insulating organic polymer and nanoparticles of an inorganic metal oxide or ferroelectric insulator having a dielectric constant of 5 or more. The dielectric constant 'k' of the first layer can be adjusted by controlling a weight ratio between the organic polymer and the organic metal compound or the nanoparticles. The dielectric constant of the first insulating layer should be controlled at 5 or higher and, in the case of the dielectric constant being less than 5, an improvement of drive properties ~~cannot be achieved~~ is more difficult to achieve due to the lower effective dielectric constant. For formation of the first layer, the mixture is coated on the substrate including the gate electrode by the wet process, and then baked.

Please replace the paragraph beginning on page 20, line 11, and ending on page 20, line 23, with the following amended paragraph:

According to the preferable embodiment of the present invention, the OTFT can be prepared by a process comprising the steps of: providing the gate electrode disposed on the substrate and forming a first layer of a high ~~K~~ k material, a second layer of an organic insulating polymer compatible with the organic active layer, the organic active layer and the source/drain electrode sequentially, wherein the first and the second layer is disposed through a wet process such as spin coating, the second layer is positioned directly beneath the organic active layer and the layering order between the organic active layer and the source/drain can be reversed.